

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	8646	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 08:40
L2	10	1 and (((inert or noble) near (element\$1 or ion\$1 or atom\$1)) same ((silicon or semiconductor or (amorphous adj silicon) or ((mono or single) adj crystalline) or ((poly adj crystalline) adj silicon)) adj (layer\$1 or film\$1))) same getter\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 08:44
S1	7530	((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 08:40
S2	202151	inert near2 gas	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/06 17:58
S3	5995238	semiconductor near\$2 (layer or film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/06 18:10
S4	389182	(metallic or metal) near2 (layer or film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/06 18:55
S5	111146	(inert near2 gas) and (semiconductor near\$2 (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/06 18:56
S6	18453	((inert near2 gas) and (semiconductor near\$2 (layer or film))) and ((metallic or metal) near2 (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/06 18:56

S7	381	(((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (((inert near2 gas) and (semiconductor near\$2 (layer or film))) and ((metallic or metal) near2 (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/06 19:04
S8	17841	getter or gettering	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/09 14:28
S9	56	(((438/143) or (438/149) or (438/310) or (438/311) or (438/471) or (438/482) or (438/488) or (438/761) or (438/762) or (438/763) or (438/764) or (438/765) or (438/778)).CCLS.) and (((inert near2 gas) and (semiconductor near\$2 (layer or film))) and ((metallic or metal) near2 (layer or film)))) and (getter or gettering)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/06 19:05
S10	509	(second near (semiconductor near2 (layer or film))) same (barrier near2 (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/09 14:28
S11	17852	getter or gettering	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/09 14:28
S12	49	((second near (semiconductor near2 (layer or film))) same (barrier near2 (layer or film))) and (getter or gettering)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/09 14:28
S13	2598	semiconductor adj energy adj laboratory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 20:51
S14	2566	(semiconductor adj energy adj laboratory) not (((second near (semiconductor near2 (layer or film))) same (barrier near2 (layer or film))) and (getter or gettering))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/09 14:29

S15	17	(((second near (semiconductor near2 (layer or film))) same (barrier near2 (layer or film))) and (getter or gettering)) not (semiconductor adj energy adj laboratory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/09 14:29
S16	1	("6686262").PN.	USPAT	OR	OFF	2004/12/09 18:11
S17	1981	yamazaki-shunpei.in.	US-PGPUB; USPAT	OR	OFF	2004/12/09 18:31
S18	806	S17 and (rare or noble or inert)	US-PGPUB; USPAT	OR	OFF	2004/12/09 18:12
S19	752	S18 and gas	US-PGPUB; USPAT	OR	OFF	2004/12/09 18:13
S20	230	S19 and (second near2 semiconductor)	US-PGPUB; USPAT	OR	OFF	2004/12/09 18:13
S21	0	yasuyaki-arai.in.	US-PGPUB; USPAT	OR	OFF	2004/12/09 18:32
S22	1	("6812081").PN.	USPAT	OR	OFF	2004/12/09 19:45
S23	1	("6048758").PN.	USPAT	OR	OFF	2004/12/09 20:27
S24	1	("6436745").PN.	USPAT	OR	OFF	2004/12/09 20:27
S25	1	("6683324").PN.	USPAT	OR	OFF	2004/12/09 20:41
S26	14662	(first and second) near2 (semiconductor near2 (film\$1 or layer\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 20:51
S27	507	S26 and getter\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 20:51
S28	3109	semiconductor adj energy adj laboratory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 16:48
S29	219	S27 not S28	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 20:52
S30	1	("6436745").PN.	USPAT	OR	OFF	2004/12/09 21:00

S31	72	(("5614426") or ("5696388") or ("20020134981") or ("20020151120") or ("20020182783") or ("5700333") or ("6303963") or ("6307214") or ("6316789") or ("6316810") or ("20020115271") or ("20020125480") or ("6133075") or ("6133119") or ("6153445") or ("6156590") or ("6156628") or ("6160268") or ("6162704") or ("6165824") or ("6168980") or ("6184559") or ("6194255") or ("6197624") or ("6201585") or ("6204101") or ("6204154") or ("6207969") or ("6218219") or ("6225152") or ("6232205") or ("6232621") or ("6242290") or ("6251712") or ("6287900") or ("6291275") or ("6294441") or ("6300659") or ("6303415") or ("5529937") or ("5608232") or ("5639698") or ("5773327") or ("5789284") or ("5814540") or ("5869363") or ("5888858") or ("5893730") or ("5897347") or ("5915174") or ("5949115") or ("5956579") or ("5961743") or ("5977559") or ("5985740") or ("6027987") or ("6048758") or ("6063654") or ("6066518") or ("6071764") or ("6071766") or ("6072193") or ("6077731") or ("6077758") or ("6084247") or ("6087679") or ("6093934") or ("6100562") or ("6111557") or ("6121660") or ("6133073") or ("5837569") or ("20021064843")).PN.	US-PGPUB; USPAT	OR	OFF	2005/05/06 16:28
S32	7	("5543636" "5707882" "5759879" "5789284" "5797999" "5837569" "5859443").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/05/06 16:21
S33	8	("4561171" "5147826" "5229306" "5244819" "5275851" "5441899" "5444001" "5529937").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/05/06 16:25
S34	0	S31 and noble	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 16:28

S35	23	S31 and inert	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 16:28
S36	10306	((("He" or helium) or ("Ne" or neon) or ("Ar" or argon) or ("Kr" or krypton) or (xe or xenon)) same ((semiconductor or amorphous or crystalline or polycrystalline) near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 17:02
S37	653	S36 and getter\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 16:45
S38	3512	semiconductor adj energy adj laboratory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 16:48
S39	287	S37 not S38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 16:49

S41	144	((("He" or helium) or ("Ne" or neon) or ("Ar" or argon) or ("Kr" or krypton) or (xe or xenon)) same (implant\$5 near2 ((semiconductor or amorphous or crystalline or polycrystalline) near2 (layer\$1 or film\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 17:03
S42	34	S41 and (getter\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 17:03
S43	14553	oxid\$5 near3 ozone	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 17:14
S44	389	S43 same ((semiconductor or amorphous or crystalline or polycrystalline) near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/06 17:15
S45	4	("5780903" "6046479" "6166397" "6207971").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/05/06 17:24